

2SC5519

Silicon NPN triple diffusion mesa type

For horizontal deflection output

■ Features

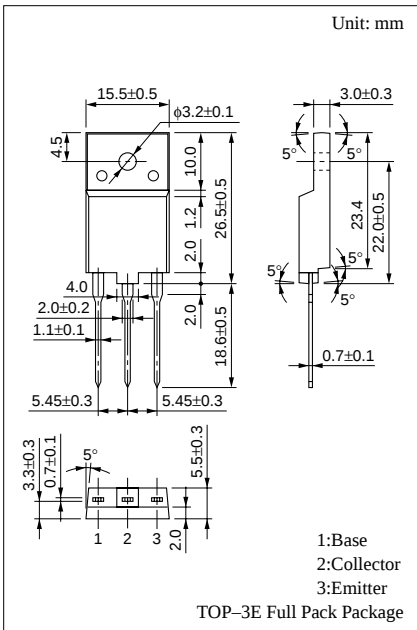
- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide area of safe operation (ASO)

■ Absolute Maximum Ratings (T_C=25°C)

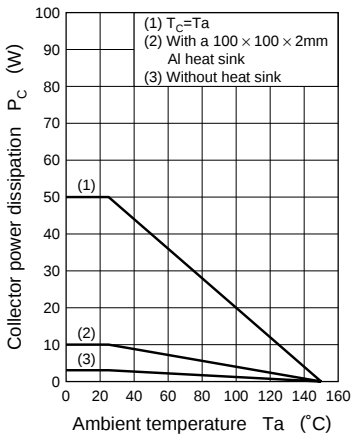
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	1700	V
Collector to emitter voltage	V _{CES}	1700	V
Emitter to base voltage	V _{EBO}	5	V
Peak collector current	I _{CP}	16	A
Collector current	I _C	8	A
Base current	I _B	3	A
Collector power dissipation	P _C	50	W
		3	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics (T_C=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 1000V, I _E = 0			50	μA
		V _{CB} = 1700V, I _E = 0			1	mA
Emitter to base voltage	V _{EBO}	I _E = 500mA, I _C = 0	5			V
Forward current transfer ratio	h _{FE}	V _{CE} = 5V, I _C = 6A	5		10	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 6A, I _B = 1.2A			3	V
Base to emitter saturation voltage	V _{BE(sat)}	I _C = 6A, I _B = 1.2A			1.5	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 0.1A, f = 0.5MHz		3		MHz
Storage time	t _{stg}	I _C = 6A, I _{B1} = 1.2A, I _{B2} = -2.4A			5.0	μs
Fall time	t _f				0.5	μs
Diode forward voltage	V _F	I _F = 6A			-2	V



$P_C - T_a$



Area of safe operation, horizontal operation ASO

